

MOSFETs Silicon N-Channel MOS (DTMOSVI)

# TK190A60Z1

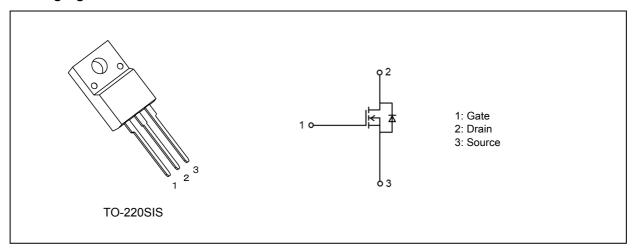
#### 1. Applications

· Switching Power Supplies

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.158 \Omega$  (typ.)
- (2) High-speed switching properties with the lower capacitance.
- (3) Enhancement mode:  $V_{th}$  = 3 to 4 V ( $V_{DS}$  = 10 V,  $I_{D}$  = 0.48 mA)

#### 3. Packaging and Internal Circuit



## 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                |                          |          | Symbol                | Rating     | Unit  |
|--------------------------------|--------------------------|----------|-----------------------|------------|-------|
| Drain-source voltage           |                          |          | V <sub>DSS</sub>      | 600        | V     |
| Gate-source voltage            |                          |          | V <sub>GSS</sub>      | ±30        | ]     |
| Drain current (DC)             |                          | (Note 1) | I <sub>D</sub>        | 14         | Α     |
| Drain current (pulsed)         |                          | (Note 1) | I <sub>DP</sub>       | 56         | ]     |
| Power dissipation              | (T <sub>c</sub> = 25 °C) |          | P <sub>D</sub>        | 40         | W     |
| Single-pulse avalanche energy  |                          | (Note 2) | E <sub>AS</sub>       | 127        | mJ    |
| Single-pulse avalanche current |                          |          | I <sub>AS</sub>       | 3.3        | Α     |
| Reverse drain current (DC)     |                          | (Note 1) | I <sub>DR</sub>       | 14         | ]     |
| Reverse drain current (pulsed) |                          | (Note 1) | I <sub>DRP</sub>      | 56         |       |
| Channel temperature            |                          |          | T <sub>ch</sub>       | 150        | °C    |
| Storage temperature            |                          |          | T <sub>stg</sub>      | -55 to 150 | ]     |
| Isolation voltage (RMS)        | (t = 1.0 s)              |          | V <sub>ISO(RMS)</sub> | 2000       | V     |
| Mounting torque                |                          |          | TOR                   | 0.6        | N · m |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

2025-09



#### 5. Thermal Characteristics

| Characteristics                       | Symbol                | Max  | Unit |
|---------------------------------------|-----------------------|------|------|
| Channel-to-case thermal resistance    |                       | 3.12 | °C/W |
| Channel-to-ambient thermal resistance | R <sub>th(ch-a)</sub> | 62.5 |      |

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25 °C (initial), L = 20.7 mH,  $I_{AS}$  = 3.3 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

### 6. Electrical Characteristics

#### 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                | Symbol               | Test Condition                                    | Min | Тур.  | Max  | Unit |
|--------------------------------|----------------------|---|-----|-------|------|------|
| Gate leakage current           | I <sub>GSS</sub>     | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$ | _   | _     | ±1   | μΑ   |
| Drain cut-off current          | I <sub>DSS</sub>     | V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V    | _   | _     | 2    |      |
| Drain-source breakdown voltage | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V     | 600 | _     | _    | V    |
| Gate threshold voltage         | $V_{th}$             | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.48 mA  | 3   | _     | 4    |      |
| Drain-source on-resistance     | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.2 A    | -   | 0.158 | 0.19 | Ω    |

## 6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

| Characteristics                               |          | Symbol             | Test Condition  | Min | Тур. | Max | Unit |
|---|----------|--------------------|---|-----|------|-----|------|
| Input capacitance                             |          | C <sub>iss</sub>   | V <sub>DS</sub> = 300 V, V <sub>GS</sub> = 0 V, f = 100 kHz | _   | 1060 | _   | pF   |
| Reverse transfer capacitance                  |          | C <sub>rss</sub>   |   | _   | 1.7  |     |      |
| Output capacitance                            |          | C <sub>oss</sub>   |   | _   | 30   | _   |      |
| Effective output capacitance (energy related) | (Note 3) | C <sub>o(er)</sub> | V <sub>DS</sub> = 0 to 400 V, V <sub>GS</sub> = 0 V         | _   | 50   |     |      |
| Effective output capacitance (time related)   | (Note 4) | C <sub>o(tr)</sub> | V <sub>DS</sub> = 0 to 400 V, V <sub>GS</sub> = 0 V         | _   | 330  |     |      |
| Gate resistance                               |          | r <sub>g</sub>     | V <sub>DS</sub> = OPEN , f = 1 MHz                          | _   | 2.8  | _   | Ω    |
| Switching time (rise time)                    |          | t <sub>r</sub>     | See Fig. 6.2.1  | _   | 18   | _   | ns   |
| Switching time (turn-on time)                 |          | t <sub>on</sub>    |   | _   | 36   | _   |      |
| Switching time (fall time)                    |          | t <sub>f</sub>     |   | _   | 5    | _   |      |
| Switching time (turn-off time)                |          | t <sub>off</sub>   |   | _   | 55   | _   |      |
| MOSFET dv/dt ruggedness                       |          | dv/dt              | $V_{DS} \le V_{DSS}$ , $I_D \le 10 \text{ A}$               | 70  | _    | _   | V/ns |

Note 3:  $C_{O(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 V to 400 V. Note 4:  $C_{O(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 V to 400 V.

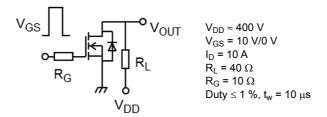


Fig. 6.2.1 Switching Time Test Circuit



## 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                                 | Symbol           | Test Condition  | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | $Q_g$            | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 14 \text{ A}$ | _   | 20   |     | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> |   |     | 6    |     |      |
| Gate-drain charge                               | $Q_{gd}$         |   | _   | 6    |     |      |

## 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics               | Symbol          | Test Condition   | Min | Тур. | Max  | Unit |
|-------------------------------|-----------------|--|-----|------|------|------|
| Diode forward voltage         | $V_{DSF}$       | I <sub>DR</sub> = 14 A, V <sub>GS</sub> = 0 V                                    | _   | _    | -1.7 | V    |
| Reverse recovery time         |                 | V <sub>DD</sub> = 400 V,   | _   | 240  | _    | ns   |
| Reverse recovery charge       | $Q_{rr}$        | I <sub>DR</sub> = 7 A, V <sub>GS</sub> = 0 V<br>-dI <sub>DR</sub> /dt = 100 A/μs | _   | 2.3  | _    | μС   |
| Peak reverse recovery current | I <sub>rr</sub> | -αιρκ/αι – 100 Α/μδ  | _   | 19   | _    | Α    |
| Diode dv/dt ruggedness        | dv/dt           | $V_{DD} \le 400 \text{ V}, I_{DR} \le 7 \text{ A}, V_{GS} = 0 \text{ V}$         | 25  | _    | _    | V/ns |

## 7. Marking (Note)

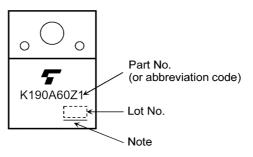


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.



## 8. Characteristics Curves (Note)

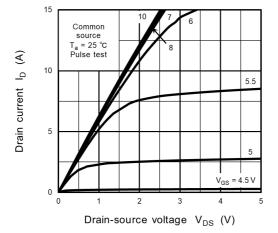


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

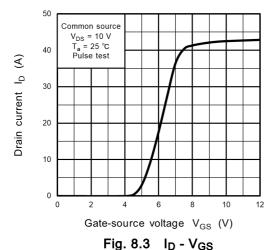


Fig. 8.5 V<sub>DSS</sub> - T<sub>a</sub>

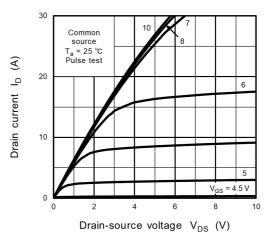


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

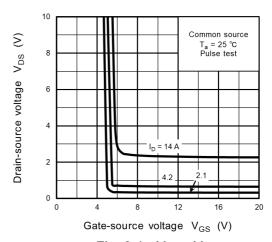


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

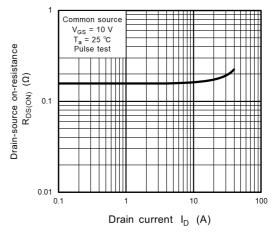
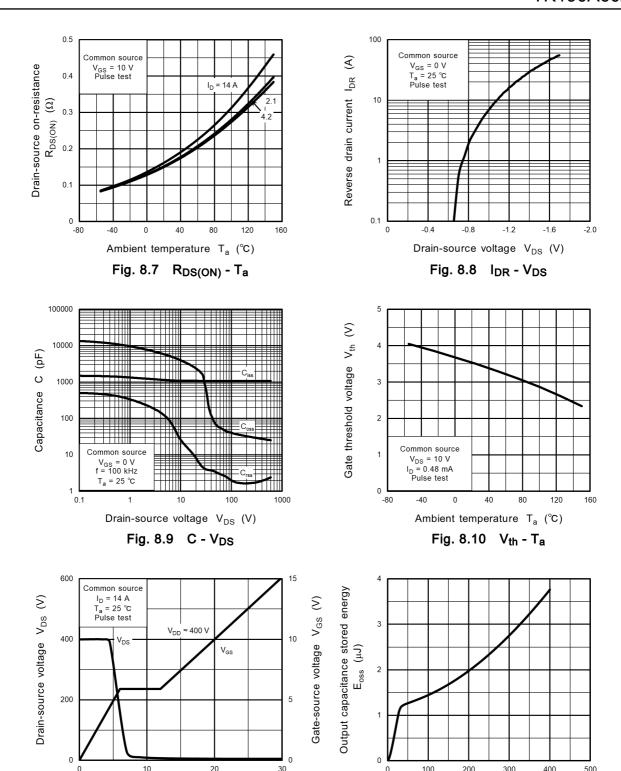


Fig. 8.6 R<sub>DS(ON)</sub> - I<sub>D</sub>





Drain-source voltage  $V_{DS}$  (V) Fig. 8.12 Eoss -  $V_{DS}$ 



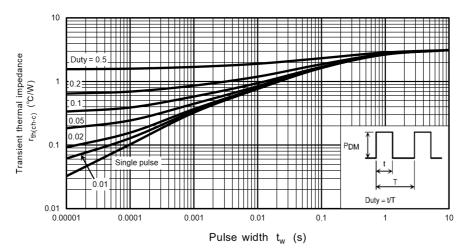


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

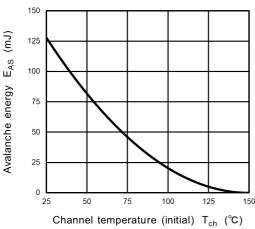
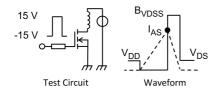


Fig. 8.14 E<sub>AS</sub> - T<sub>ch</sub> (Guaranteed Maximum)



$$V_{DD} = 90 \text{ V, L} = 20.7 \text{ mH}$$
  $E_{AS} = \frac{1}{2} \cdot \text{L} \cdot \text{I}_{AS}^2 \cdot \left( \frac{\text{B}_{VDSS}}{\text{B}_{VDSS} - \text{V}_{DD}} \right)$ 

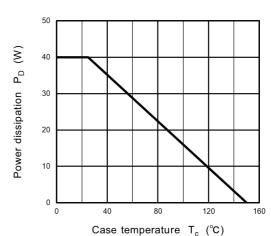


Fig. 8.15 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

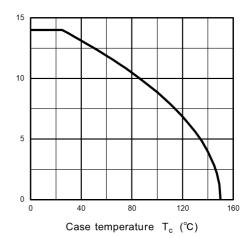


Fig. 8.17 I<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

Fig. 8.16 Test Circuit/Waveform

Drain current I<sub>D</sub> (A)



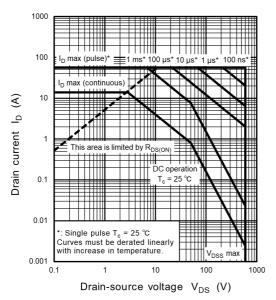


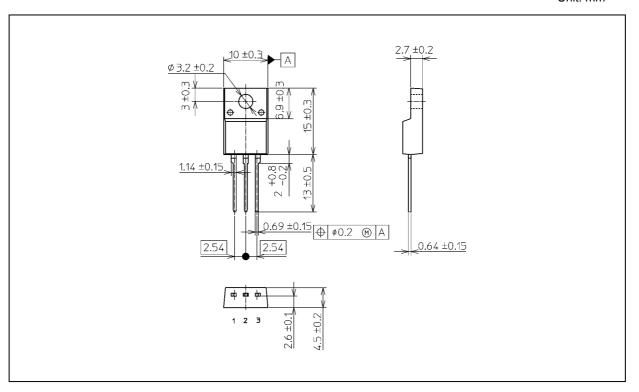
Fig. 8.18 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 1.7 g (typ.)

| Package Name(s)     |  |
|---------------------|--|
| TOSHIBA: 2-10U1S    |  |
| Nickname: TO-220SIS |  |



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